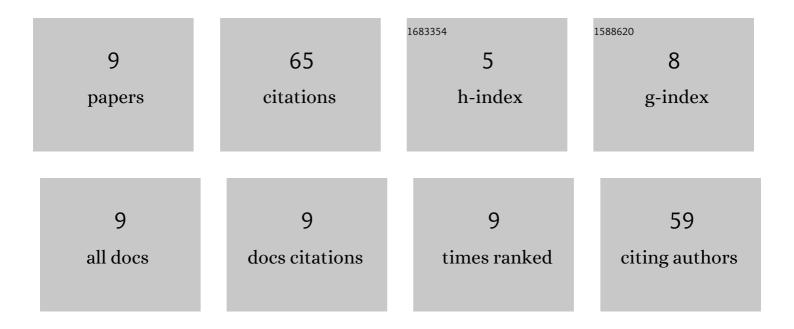
Andreas Sattler

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|---|---|-----|-----------|
| 1 | Analysis of the Nucleation Kinetics of Oxide Precipitates in Czochralski Silicon. ECS Transactions, 2008, 16, 97-108. | 0.3 | 17 |
| 2 | 3D unsteady and steady modeling of heat and mass transfer during Cz Si crystal growth with a horizontal magnetic field. International Journal of Heat and Mass Transfer, 2021, 178, 121604. | 2.5 | 14 |
| 3 | Combination of optical measurement and precipitation theory to overcome the obstacles of detection limits. Materials Science in Semiconductor Processing, 2006, 9, 236-240. | 1.9 | 7 |
| 4 | Ab initio calculations and rate equation simulations for vacancy and vacancy-oxygen clustering in silicon. Journal of Crystal Growth, 2017, 468, 424-432. | 0.7 | 7 |
| 5 | Thermodynamic and morphological analysis of large silicon self-interstitial clusters using atomistic simulations. Journal of Applied Physics, 2015, 117, 135706. | 1.1 | 5 |
| 6 | Defects in Monocrystalline Silicon. Springer Handbooks, 2017, , 1-1. | 0.3 | 5 |
| 7 | Evaluation of the Performance of Published Point Defect Parameter Sets in Cone and Body Phase of a 300 mm Czochralski Silicon Crystal. Crystals, 2021, 11, 460. | 1.0 | 4 |
| 8 | Data-assisted physical modeling of oxygen precipitation in silicon wafers. Journal of Applied Physics, 2019, 125, 165705. | 1.1 | 3 |
| 9 | Editors' Choice—Precipitation of Suboxides in Silicon, their Role in Gettering of Copper Impurities and Carrier Recombination, ECS Journal of Solid State Science and Technology, 2020, 9, 064002 | 0.9 | 3 |